

“Comparison of short-channel effects in monolayer MoS₂ based junctionless and inversion mode field-effect transistors”. Agarwal T, Sorée B, Radu I, Raghavan P, Fiori G, Iannaccone G, Thean A, Heyns M, Dehaene W, Applied physics letters **108**, 023506 (2016).
<http://doi.org/10.1063/1.4939933>